

2SC3858

Silicon NPN Triple Diffused Planar Transistor (Complement to type 2SA1494)

Application : Audio and General Purpose

Absolute maximum ratings (Ta=25°C)

Symbol	2SC3858	Unit
VCBO	200	V
VCEO	200	V
VEBO	6	V
IC	17	A
IB	5	A
PC	200(Tc=25°C)	W
TJ	150	°C
Tstg	-55 to +150	°C

Electrical Characteristics (Ta=25°C)

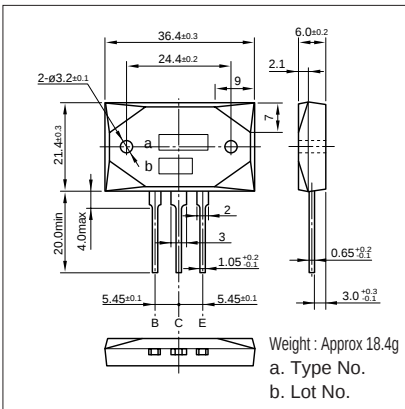
Symbol	Conditions	2SC3858	Unit
ICBO	VCB=200V	100max	μA
IEBO	VEB=6V	100max	μA
V(BR)CEO	IC=50mA	200min	V
hFE	VCE=4V, IC=8A	50min*	
VCE(sat)	IC=10A, IB=1A	2.5max	V
fr	VCE=12V, IE=-1A	20typ	MHz
COB	VCB=10V, f=1MHz	300typ	pF

*hFE Rank Y(50 to 100), P(70 to 140), G(90 to 180)

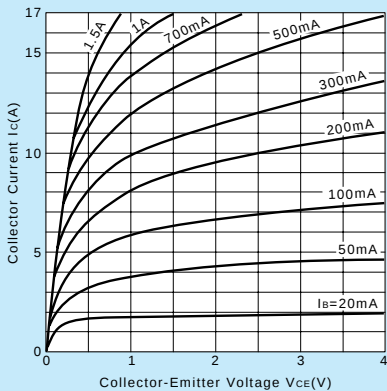
Typical Switching Characteristics (Common Emitter)

VCC (V)	RL (Ω)	IC (A)	VBB1 (V)	VBB2 (V)	IB1 (A)	IB2 (A)	ton (μs)	tstg (μs)	tf (μs)
40	4	10	10	-5	1	-1	0.5typ	1.8typ	0.6typ

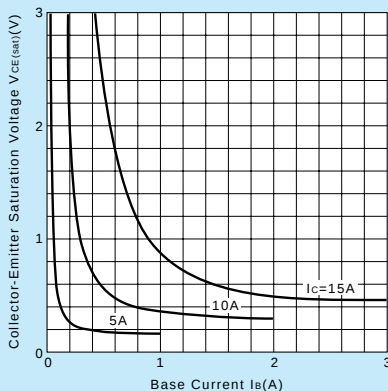
External Dimensions MT-200



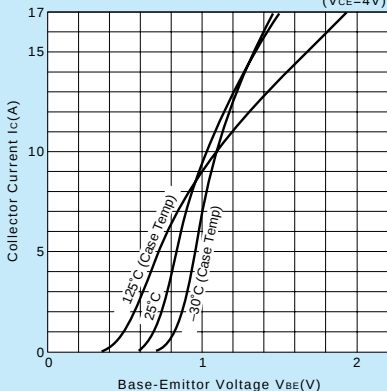
IC-VCE Characteristics (Typical)



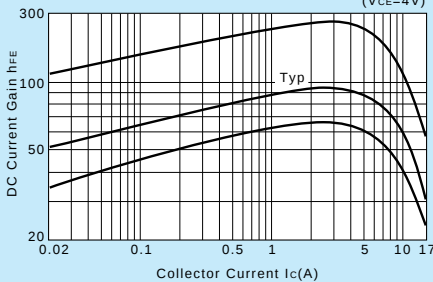
VCE(sat)-IB Characteristics (Typical)



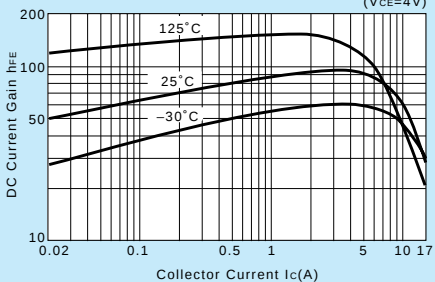
IC-VBE Temperature Characteristics (Typical)



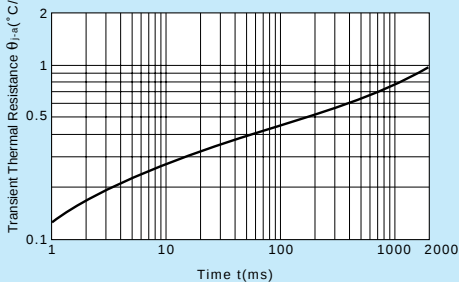
hFE-IC Characteristics (Typical)



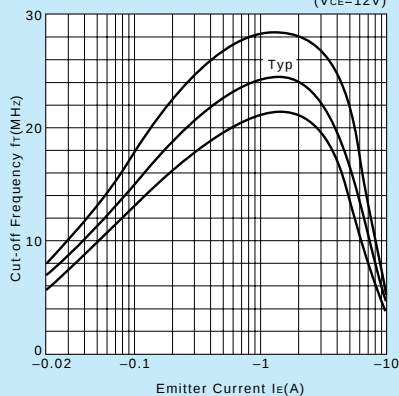
hFE-IC Temperature Characteristics (Typical)



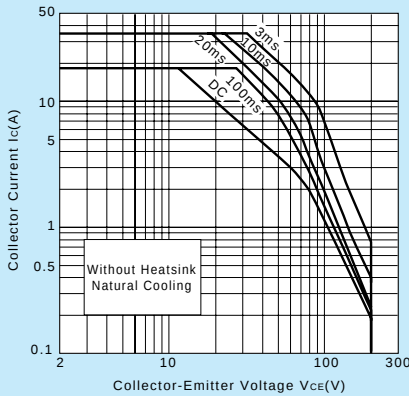
θj-a-t Characteristics



fr-IE Characteristics (Typical)



Safe Operating Area (Single Pulse)



Pc-Ta Derating

